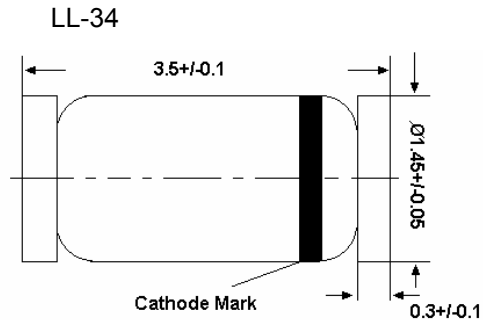


LL914...LL4454

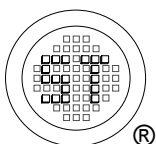
SILICON EPITAXIAL PLANAR DIODES

for General Purpose and Switching.



Glass case MiniMELF
Dimensions in mm

Type	Peak reverse voltage $V_{RM}V$	Max. aver. rectified current I_OmA	Max. power dissip. at 25°C $P_{tot}mW$	Max. junction temperature $T_j^{\circ}C$	Max. forward voltage drop		Max. reverse current		Max. reverse recovery time	
					V_FV	at I_FmA	I_nnA	at V_RV	$t_{rr}ns$	Conditions
LL914	100	75	500	200	1.0	10	25	20	max.4.0	$I_F = 10mA, V_R = 6V, R_L = 100\Omega, \text{ to } I_R = 1mA$
LL4149	100	150	500	200	1.0	10	25	20	max.4.0	$I_F = 10mA, V_R = 6V, R_L = 100\Omega, \text{ to } I_R = 1mA$
LL4151	75	150	500	200	1.0	50	50	50	max.2.0	$I_F = 10mA, V_R = 6V, R_L = 100\Omega, \text{ to } I_R = 1mA$
LL4152	40	150	400	175	0.55	0.10	50	30	max.2.0	$I_F = 10mA, V_R = 6V, R_L = 100\Omega, \text{ to } I_R = 1mA$
LL4153	75	150	400	175	0.55	0.10	50	50	max.2.0	$I_F = 10mA, V_R = 6V, R_L = 100\Omega, \text{ to } I_R = 1mA$
LL4154	35	150	500	200	1.0	30	100	25	max.2.0	$I_F = 10mA, V_R = 6V, R_L = 100\Omega, \text{ to } I_R = 1mA$
LL4447	100	150	500	200	1.0	20	25	20	max.4.0	$I_F = 10mA, V_R = 6V, R_L = 100\Omega, \text{ to } I_R = 1mA$
LL4449	100	150	500	200	1.0	30	25	20	max.4.0	$I_F = 10mA, V_R = 6V, R_L = 100\Omega, \text{ to } I_R = 1mA$
LL4450	40	150	400	175	0.54	0.50	50	30	max.4.0	$I_F = I_R = 10mA, \text{ to } I_R = 1mA$
LL4451	40	150	400	175	0.50	0.10	50	30	max.10	$I_F = I_R = 10mA, \text{ to } I_R = 1mA$
LL4453	30	150	400	175	0.55	0.01	50	20	-	-
LL4454	75	150	400	175	1.0	10	100	50	max.4.0	$I_F = I_R = 10mA, \text{ to } I_R = 1mA$



SEMTECH ELECTRONICS LTD.

(Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)



ISO/TS 16949 : 2002
Certificate No. 05103



ISO 14001:2004
Certificate No. 7116



ISO 9001:2000
Certificate No. 0506098

Dated : 12/02/2003